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This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SENT FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patente, P.O. Box 1650, Alexandria, Virginia 22313-1450.

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SENT FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450. If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.

Form PTO-1449 (Modified) Atty Docket No.: P18609 Serial No.: Unknown-10828928 List of Patents and Publications Statement Applicant: Justin K. Brask (Use several sheets if necessary) Filing Date: April 20, 2004 REFERENCE DESIGNATION **U.S. PATENT DOCUMENTS** Document No. Examiner Class Sub-Filing date Initials Class if appropriate SOW AA 6,063,698 Tseng et al. 438 585 AB 6,184,072 B1 Kaushik et al. 438 197 AC 6,420,279 B1 Ono et al. 438 785 AD 6,475,874 B2 Xiang et al. 438 396 AE 6,514,828 B2 Ahn et al. 438 240 AF 6,544,906 B2 Rotondaro et al. 438 785 AG 6,617,209 B1 Chau et al. 438 240 AH 6,617,210 B1 Chau et al. 240 438 ΑÏ 6,620,713 B2 Arghavani et al. 438 585 AJ 6,689,675 B1 438 Parker et al. 585 AK 6,696,327 B1 Brask et al. 438 197 AL 6,696,345 B2 Chau et al. 438 387 AM US2002/0197790 A1 Kizilyalli et al. 438 240 770 AN US2003/0032303 A1 Yu et al. 438 ODa AO US2003/0045080 A1 Visokay et al. 438 591 FOREIGN PATENT DOCUMENTS Document No. Date Country Class Sub-Class Translation AP OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.) Polishchuk et al., "Dual Workfunction CMOS Gate Technology Based on Metal Interdiffusion", ω AQ www.eesc.berkeley.edu, 1 page Doug Barlage et al., "High-Frequency Response of 100nm Integrated CMOS Transistors with High-K Gate Dielectrics", 2001 IEEE, 4 pages Lu et al., "Dual-Metal Gate Technology for Deep-Submicron CMOS Devices", dated April 29, 2003, 1 page AS Schwantes et al., "Performance Improvement of Metal Gate CMOS Technologies with Gigabit Sign Feature Sizes", Technical University of Hanburg-Harburg, 5 pages AΤ Doczy et al. "Integrating N. typerand P. typerMetal Gate Transistors," Serial No. 10/327,293, Filed December 20, 2002 AU Brask et al., "A Method for Making a Semiconductor Device Having a Metal Gate Electrode," ΑV Serial No. 10/704,497, Filed November 6, 2003 Brask et al., "A Method for Etching a Thin Metal Layer" Serial No. 10/704,498, Filed November AW 6, 2003 Brask et al., "A Method for Making a Semiconductor Device with a Metal Gate Electrode that is Formed on an Annealed High-K Gate Dielectric Cayer", Serial No. 10/742,678, Filed 12/19/03 AX Brask et al., "A Method for Making a Semiconductor Device that Includes a Metal Gate Electronic, Serial No. 10/739,173, filed December 18, 2003 AY Brask et al., "A CMOS Device With Metal and Silicide Gate Electrodes and a Method for Making AZ It, Serial No. 10/748,559, filed December 29, 2003 Doczy et al., "A Method for Making a Semiconductor Device that Includes a Metal Gate Electrode Serial No. 10/748,545, filed December 29, 2003 Shah et al., "A Method for Making a Semiconductor Device with a Metal Gate Electrode," Serial No.-10/805,880, filed March 22, 2004. BB Shah et al., "A Replacement Gte Process for Making a Semiconductor Device that Includes a Metal Gate Electrode," Serial No. 10/809,853, filed March 24, 2004. BC Examiner Christian Date Considered いころり EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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